

Vishay Siliconix

P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)			
- 30	0.053 at V _{GS} = - 10 V	- 4.0			
	0.086 at V _{GS} = - 4.5 V	- 3.1			

FEATURES

- Halogen-free According to IEC 61249-2-21
 Available
- TrenchFET[®] Power MOSFET

APPLICATIONS

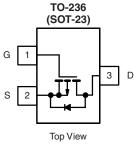
- Load Switch
- PA Switch



COMPLIANT

HALOGEN

Available



Si2343DS (F3)* * Marking Code

Ordering Information: Si2343DS-T1

Si2343DS-T1-E3 (Lead (Pb)-free)

Si2343DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	ss otherwise r	noted		
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 30		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Durin Current (T. 150 %C)& b	T _A = 25 °C	I _D	- 4.0	- 3.1	
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 70 °C		- 3.2	- 2.5	
Pulsed Drain Current		I _{DM}	- 15		A
Continuous Source Current (Diode Conduction) ^{a, b}		۱ _S	- 1.0	- 0.6	
Marian Dissission a b	T _A = 25 °C	P	1.25 0.75		W
Maximum Power Dissipation ^{a, b}	T _A = 70 °C	– P _D	0.8	0.48	vv
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
	t ≤ 5 s	R _{thJA}	75	100	
Maximum Junction-to-Ambient ^a	Steady State		120	166	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	40	50	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. Pulse width limited by maximum junction temperature.

* Pb containing terminations are not RoHS compliant, exemptions may apply

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					Limits		
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0$ V, $I_D = -250$ μ A	- 30			v	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$	- 1		- 3		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = -24 V, V_{GS} = 0 V$			- 1	μΑ	
	IDSS	V_{DS} = - 24 V, V_{GS} = 0 V, T_{J} = 55 °C			- 10		
On-State Drain Current ^a	I _{D(on)}	V_{DS} \leq - 5 V, V_{GS} = - 10 V	- 15			А	
Drain-Source On-Resistance ^a	Б	V _{GS} = - 10 V, I _D = - 4.0 A		0.043	043 0.053	0	
	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -3.1 \text{ A}$		0.068	0.086	Ω	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = -5 V, I_{D} = -4.0 A$		10		S	
Diode Forward Voltage	V _{SD}	I _S = - 1.0 A, V _{GS} = 0 V		- 0.7	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Qg			14	21	nC	
Gate-Source Charge	Q _{gs}	V _{DS} = - 15 V, V _{GS} = - 10 V I _D ≅ - 4.0 A		1.9			
Gate-Drain Charge	Q _{gd}	D = -4.0 A		3.7			
Input Capacitance	C _{iss}			540		pF	
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$		131			
Reverse Transfer Capacitance	C _{rss}			105		1	
Switching ^c							
Turn On Time	t _{d(on)}			10	15	- ns	
Turn-On Time	t _r	$V_{DD} = -15 V, R_L = 15 \Omega$		15	25		
Turne Off Time	t _{d(off)}	$I_D \cong$ - 1.0 A, V_{GEN} = - 10 V R _G = 6 Ω		31	50		
Turn-Off Time	t _f	1.6 - 0.22		20	30		

Notes:

a. Pulse test: PW \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. For DESIGN AID ONLY, not subject to production testing.

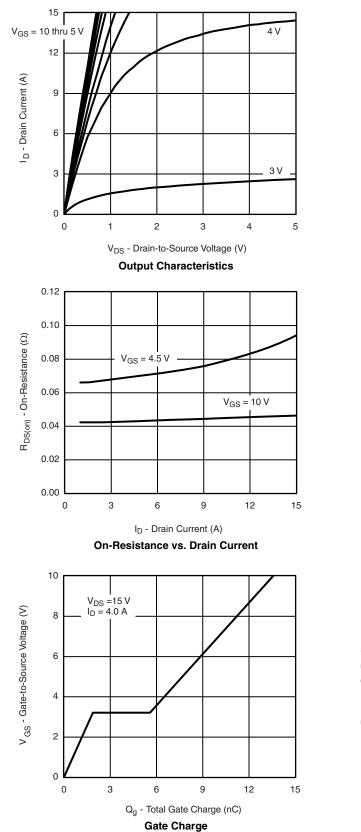
c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

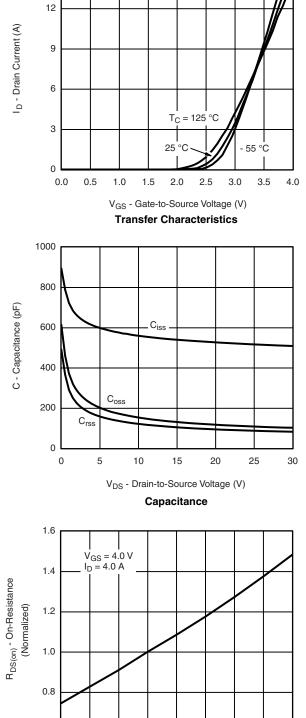


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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



15

0.6

- 50

- 25

0

25

50

T_J - Junction Temperature (°C)

On-Resistance vs. Junction Temperature

75

100

125

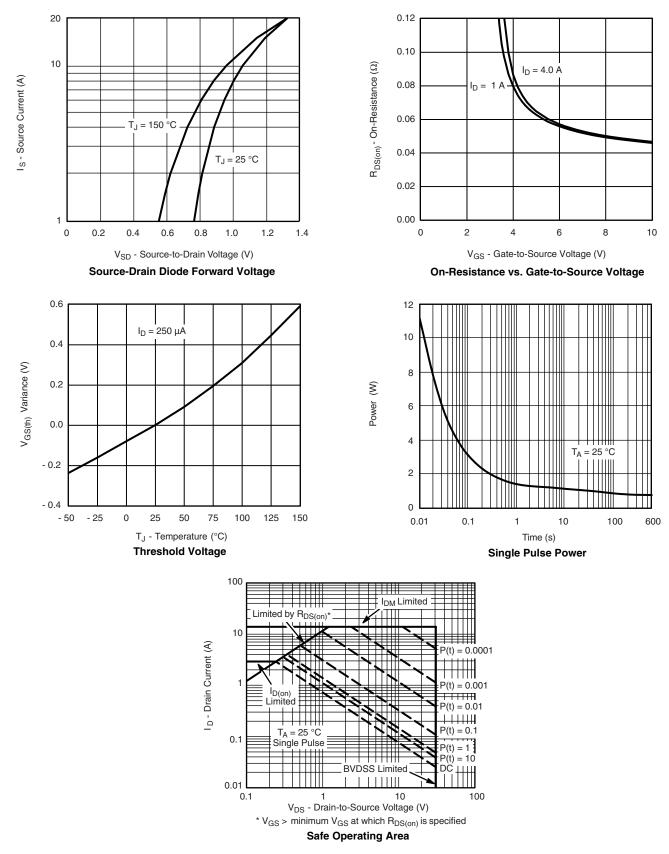
150

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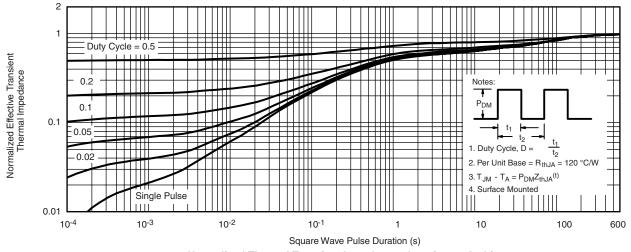
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

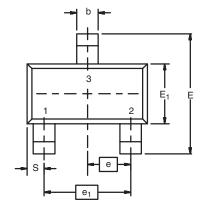
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?72079</u>.



Package Information

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SOT-23 (TO-236): 3-LEAD







Dim	MILLIN	METERS	INCHES		
	Min	Max	Min	Мах	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	



Application Note 826

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RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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